

ABSTRACT

An island-like interlayer insulating film is formed selectively in a region where a source interconnection and a gate interconnection intersect. For example, by use of
5 ink jet method, a solution containing an insulating material is dropped on a region where the gate interconnection and the source interconnection intersect or a region where a holding capacitor is formed, that enable to reduce a photolithography process and to reduce the number of masks that are used in a TFT